

# ZXTP2008Z

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## 30V PNP LOW SATURATION MEDIUM POWER TRANSISTOR IN SOT89

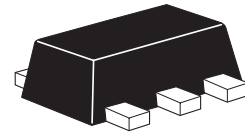
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### SUMMARY

$BV_{CEO} = -30V$  ;  $R_{SAT} = 24m\Omega$ ;  $I_C = -5.5A$

### DESCRIPTION

Packaged in the SOT89 outline this new low saturation 30V PNP transistor offers low on state losses making it ideal for use in DC-DC circuits, line switching and various driving and power management functions.



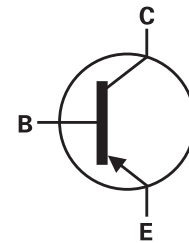
SOT89

### FEATURES

- 5.5 amps continuous current
- Up to 20 amps peak current
- Very low saturation voltages
- Exceptional gain linearity down to 10mA
- Excellent high current gain hold up

### APPLICATIONS

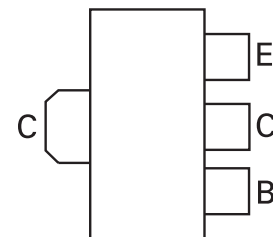
- DC - DC converters
- MOSFET gate drivers
- Charging circuits
- Power switches
- Motor control



### ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXTP2008ZTA	7"	12mm embossed	1000 units

### PINOUT



TOP VIEW

### DEVICE MARKING

949

# ZXTP2008Z

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-base voltage	$BV_{CBO}$	-50	V
Collector-emitter voltage	$BV_{CEO}$	-30	V
Emitter-base voltage	$BV_{EBO}$	-7	V
Continuous collector current <sup>(a)</sup>	$I_C$	-5.5	A
Peak pulse current	$I_{CM}$	-20	A
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(a)</sup>	$P_D$	1.5	W
Linear derating factor		12	mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(b)</sup>	$P_D$	2.1	W
Linear derating factor		16.8	mW/°C
Operating and storage temperature range	$T_j, T_{stg}$	-55 to 150	°C

## THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient <sup>(a)</sup>	$R_{\theta JA}$	83	°C/W
Junction to Ambient <sup>(b)</sup>	$R_{\theta JA}$	60	°C/W

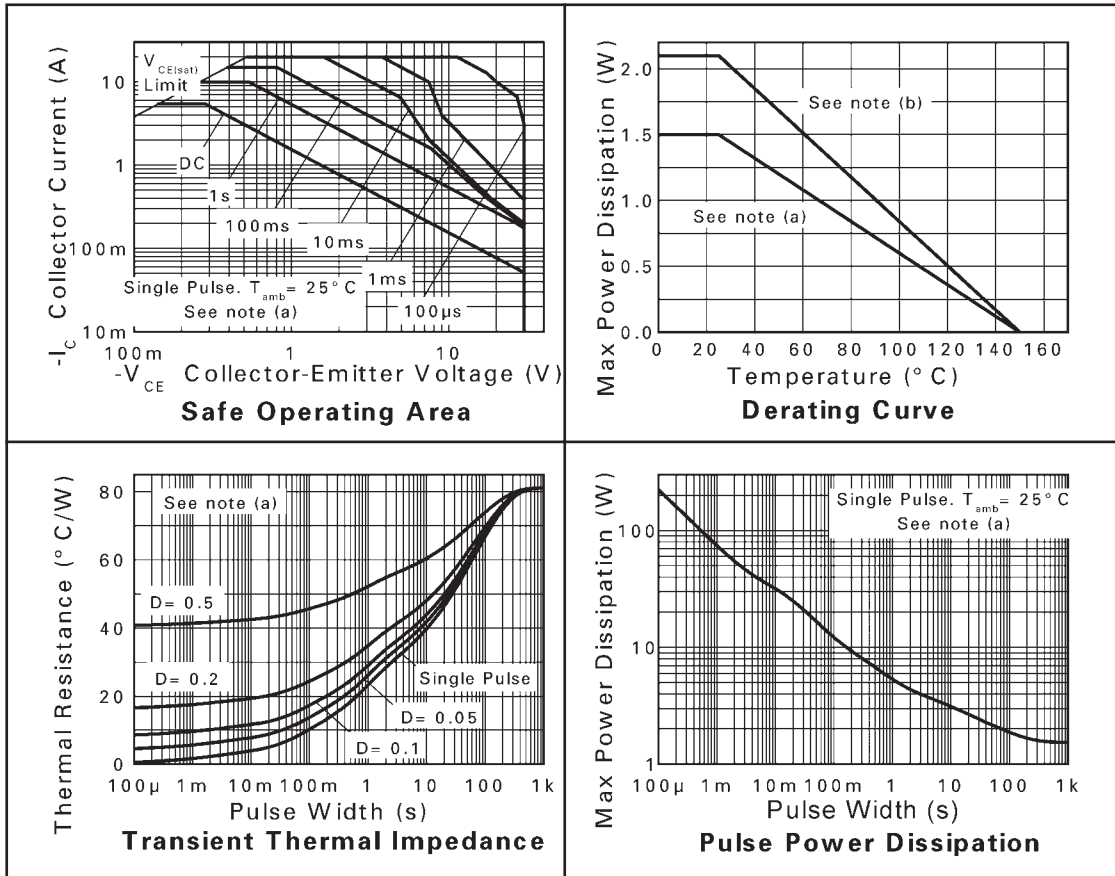
### NOTES

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

# ZXTP2008Z

## CHARACTERISTICS



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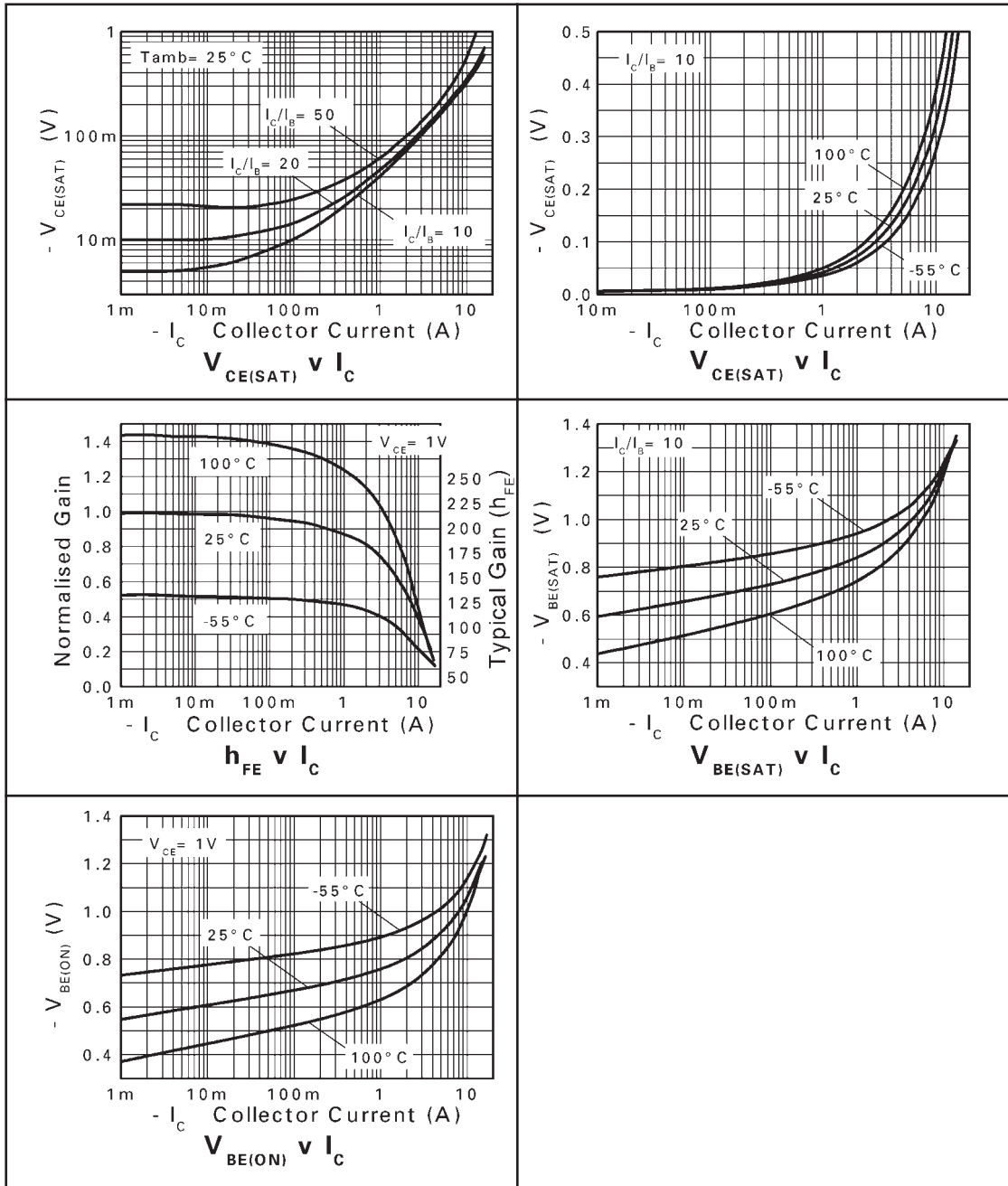
## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-base breakdown voltage	$BV_{CBO}$	-50	-70		V	$I_C = -100\mu\text{A}$
Collector-emitter breakdown voltage	$BV_{CER}$	-50	-70		V	$I_C = -1\mu\text{A}$ , $R_B < 1\text{k}\Omega$
Collector-emitter breakdown voltage	$BV_{CEO}$	-30	-40		V	$I_C = -10\text{mA}$ *
Emitter-base breakdown voltage	$BV_{EBO}$	-7.0	-8.0		V	$I_E = -100\mu\text{A}$
Collector cut-off current	$I_{CBO}$		<-1	-20 -0.5	nA $\mu\text{A}$	$V_{CB} = -40\text{V}$ $V_{CB} = -40\text{V}$ , $T_{amb} = 100^{\circ}\text{C}$
Collector cut-off current	$I_{CER}$ $R < 1\text{k}\Omega$		<-1	-20 -0.5	nA $\mu\text{A}$	$V_{CB} = -40\text{V}$ $V_{CB} = -40\text{V}$ , $T_{amb} = 100^{\circ}\text{C}$
Emitter cut-off current	$I_{EBO}$		<-1	-10	nA	$V_{EB} = -6\text{V}$
Collector-emitter saturation voltage	$V_{CE(SAT)}$		-25 -35 -55 -55 -130	-40 -55 -80 -80 -175	mV mV mV mV mV	$I_C = -0.5\text{A}$ , $I_B = -20\text{mA}$ * $I_C = -1\text{A}$ , $I_B = -100\text{mA}$ * $I_C = -1\text{A}$ , $I_B = -20\text{mA}$ * $I_C = -2\text{A}$ , $I_B = -200\text{mA}$ * $I_C = -5.5\text{A}$ , $I_B = -500\text{mA}$ *
Base-emitter saturation voltage	$V_{BE(SAT)}$		-970	-1070	mV	$I_C = -5.5\text{A}$ , $I_B = -500\text{mA}$ *
Base-emitter turn-on voltage	$V_{BE(ON)}$		-860	-960	mV	$I_C = -5.5\text{A}$ , $V_{CE} = -1\text{V}$ *
Static forward current transfer ratio	$h_{FE}$	100 100 70 10	225 200 145 20	300		$I_C = -10\text{mA}$ , $V_{CE} = -1\text{V}$ * $I_C = -1\text{A}$ , $V_{CE} = -1\text{V}$ * $I_C = -5\text{A}$ , $V_{CE} = -1\text{V}$ * $I_C = -20\text{A}$ , $V_{CE} = -1\text{V}$ *
Transition frequency	$f_T$		110		MHz	$I_C = -100\text{mA}$ , $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$
Output capacitance	$C_{OBO}$		83		pF	$V_{CB} = -10\text{V}$ , $f = 1\text{MHz}$ *
Switching times	$t_{ON}$ $t_{OFF}$		43 230		ns	$I_C = -1\text{A}$ , $V_{CC} = -10\text{V}$ , $I_{B1} = -I_{B2} = -100\text{mA}$

### NOTES

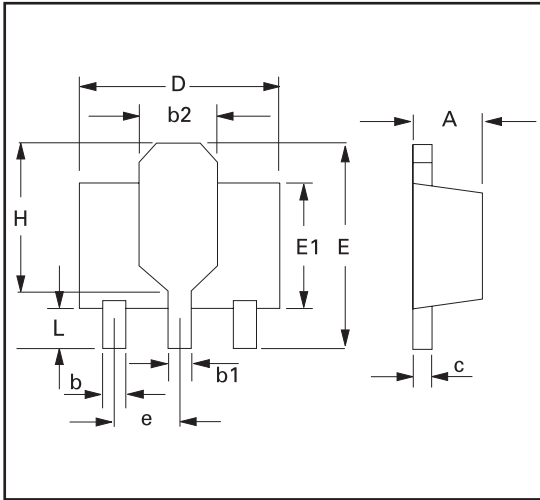
\* Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

TYPICAL CHARACTERISTICS

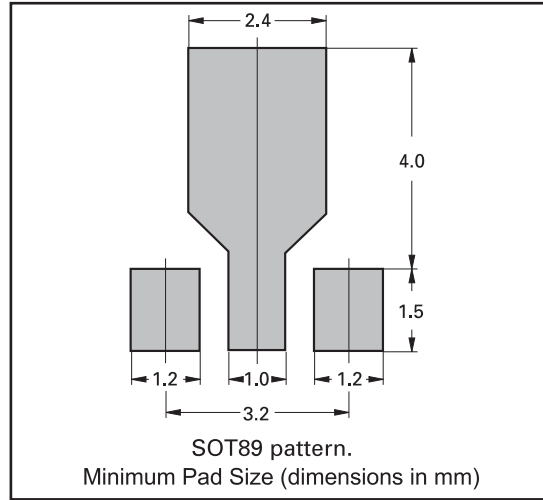


# ZXTP2008Z

## PACKAGE OUTLINE



## PAD LAYOUT DETAILS



Controlling dimensions are in millimeters. Approximate conversions are given in inches

## PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	e	1.40	1.50	0.055	0.059
b	0.38	0.48	0.015	0.019	E	3.75	4.25	0.150	0.167
b1	-	0.53	-	0.021	E1	-	2.60	-	0.102
b2	1.50	1.80	0.060	0.071	G	2.90	3.00	0.114	0.118
c	0.28	0.44	0.011	0.017	H	2.60	2.85	0.102	0.112
D	4.40	4.60	0.173	0.181	-	-	-	-	-

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Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Streitfeldstraße 19 D-81673 München Germany	Zetex Inc 700 Veterans Memorial Hwy Hauppauge, NY 11788 USA	Zetex (Asia) Ltd 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park Chadderton, Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 <a href="mailto:europa.sales@zetex.com">europa.sales@zetex.com</a>	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 <a href="mailto:usa.sales@zetex.com">usa.sales@zetex.com</a>	Telephone: (852) 26100 611 Fax: (852) 24250 494 <a href="mailto:asia.sales@zetex.com">asia.sales@zetex.com</a>	Telephone (44) 161 622 4444 Fax: (44) 161 622 4446 <a href="mailto:hq@zetex.com">hq@zetex.com</a>

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